## **Supplementary Data**

## In-situ reversibly tuning photoluminescence of epitaxial thin film via piezoelectric strain induced by Pb(Mg<sub>1/3</sub>Nb<sub>2/3</sub>)O<sub>3</sub>-PbTiO<sub>3</sub> single crystal

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**Fig. S1** shows the schematic PFM set-up and the local PFM hysteresis loops measured under 25 V dc bias field and an ac voltage of 1 V was applied. The phase angle exhibited a 180°change under the reversal of the dc bias field, confirming a polarization switching process.

Fig. S2 shows the macroscopic P-E loops of the BTO(Yb/Er) thin film, it can

been found that the maximum polarization  $P_{\rm m}$ , remnant polarization  $P_{\rm r}$ , and coercive field  $E_{\rm c}$  is ~30  $\mu$ C/cm<sup>2</sup>, ~10  $\mu$ C /cm<sup>2</sup> and 3 kV/mm, respectively. The well-defined hysteresis loops verified the macroscopic ferroelectric response of the epitaxial BTO(Yb/Er) thin film.

**Fig. S3** shows the cross-sectional HRTEM image of the SRO/BTO(Yb/Er) interface, which indicated the BTO(Yb/Er) thin film was epitaxially grown on the SRO bottom electrode.

**Fig. S4** shows the PL spectra measured under 0.3 kV/mm during the increasing and decreasing process. It can be found that in the repeated process the intensity of the green emission peak was reversibly changed.



Fig. S1. The PFM set-up and local piezoelectric hysteresis loop of the BTO(Yb/Er)

thin film.



Fig. S2. The macroscopic P-E loops of the BTO(Yb/Er) thin film measured under 1



kHz at room temperature.

Fig. S3. The cross-sectional HRTEM image of the SRO/BTO(Yb/Er) interface.



Fig. S4. The PL spectra measured under 0.3 kV/mm during the increasing and

decreasing process